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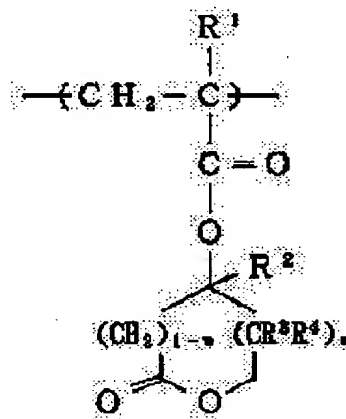
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(54) CHEMICAL AMPLIFICATION TYPE PHOTORESIST COMPOSITION

(57)Abstract:

PROBLEM TO BE SOLVED: To obtain a photoresist compsn. having high transparency to ArF excimer laser light, exhibiting superior sensitivity, resist pattern shape, dry etching resistance and adhesion and having high affinity for an alkali by incorporating acrylic resin having specified constituent units and an acid generating agent.

SOLUTION: This photoresist compsn. contains acrylic resin whose alkali solubility is varied by the action of an acid and an acid generating agent. The acrylic resin is a (meth)acrylic acid (co)polymer having constituent units represented by the formula as at least part of the constituent units. In the formula, R1 is H or methyl, each of R2-R4 is H, lower alkyl or lower alkoxy and (n) is 0 or 1. The acrylic resin may be a copolymer of a deriv. of acrylic acid having a dry etching resistance improving group or an acid dissociability protecting group with unsatd. carboxylic acid and other monomer.



LEGAL STATUS

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